STGD4H60DF-VB Datasheet

600V Trench and Fieldstop IGBT

PRODUCT SUMMARY		
V_{CE} (V)	600	
I_C (A)	14 (TC=25°C)	7(TC=100°C)
V_{CE} (sat) (V)	1.6	
I_{CM} (A)	21	

FEATURES

- Very Low VCEsat
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)

RoHS COMPLIANT
HALOGEN FREE

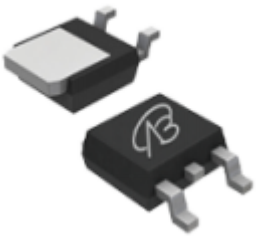
APPLICATIONS

- Telecommunications
  - Server and telecom power supplies
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Consumer and computing
  - ATX power supplies
- Industrial
  - Welding
  - Battery chargers

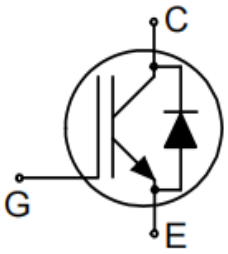
Renewable energy
- Solar (PV inverters)

Switch mode power supplies (SMPS)

TO-252



Top View



Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)					
PARAMETER			**SYMBOL**	**LIMIT**	**UNIT**
Collector-Emitter Voltage			V_{CE}	600	V
Gate-Emitter Voltage			V_{GE}	±30	
Continuous Collector Current (T_J = 150 °C)	V_{GE} at 15 V	T_C = 25 °C	I_C	14	A
		T_C = 100 °C		7	
Pulsed Collector Current [a]			I_{CM}	21	
Diode Forward Current [b]			I_F	7	A
Maximum Power Dissipation		T_C = 25 °C	P_D	55	W
		T_C = 100 °C		43	W
Operating Junction and Storage Temperature Range			T_J, T_{stg}	-55 to +175	°C
Short Circuit Withstand Time TC=150°C	VGE= 15V, VCE≤ 400V		t_{SC}	3	µs
Short Circuit Withstand Time TC=100°C	VGE= 15V, VCE≤330V			5	
Soldering Recommendations (Peak Temperature) [c]	for 10 s			260	°C

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature.

b. Current limited by maximum junction temperature.

c. 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case	R_{thJC}	-	1.5	

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Collector-Emitter Breakdown Voltage	BV_{CE}	V_{GE} = 0 V, I_C = 250 µA V_{GE} = 0 V, I_C = 1 mA	600 600	- -	- -	V
Gate-Source Threshold Voltage (N)	$V_{GE(th)}$	V_{CE} = V_{GE}, I_D = 250 µA	4	5	6	V
Zero Gate Voltage Collector Current	I_{CES}	V_{CE} = 600 V,V_{GE} = 0 V,T_J = 25 °C	-	1	20	µA
		V_{CE} = 600 V,V_{GE} = 0 V,T_J = 150 °C	-	1000	-	µA
Gate-Emitter Leakage Current	I_{GES}	V_{CE} = 0 V, V_{GS} = ± 2 0 V	-	-	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	V_{GE} = 15 V, I_C = 7 A	-	1.7	2.1	V
Forward Transconductance	g_{fs}	V_{CE} = 20 V, I_C = 7 A	-	40	-	S
Dynamic						
Input Capacitance	C_{ies}	V_{GE} = 0 V, V_{CE} = 25 V, f = 500 KHz	-	1400	-	pF
Output Capacitance	C_{oes}		-	76	-	
Reverse Transfer Capacitance	C_{res}		-	21	-	
Turn-on Energy	E_{on}	V_{CE} = 400 V , V_{GE} = 0 /15V, I_C = 7 A, R_g = 10Ω	-	0.81	-	nJ
Turn-off Energy	E_{off}		-	0.26	-	
Total Gate Charge	Q_g	V_{GE} = 15 V, I_C = 7 A, V_{CE} = 400 V	-	18	-	nC
Gate-Emitter Charge	Q_{ge}		-	15	-	
Gate to Collector Charge	Q_{gc}		-	33	-	
Turn-On Delay Time	$t_{d(on)}$	V_{CE} = 400 V , V_{GE} = 0 /15V, I_C = 7 A, R_g = 10Ω	-	45	-	ns
Rise Time	t_r		-	25	-	
Turn-Off Delay Time	$t_{d(off)}$		-	115	-	
Fall Time	t_f		-	24	-	
Internal emitter inductance measured 5 mm	L_E		-	13	-	nH
Diode Characteristics						
Diode Forward Current	I_F	IGBT symbol showing the integral reverse junction diode	-	-	7	A
Pulsed Diode Forward Current	I_{FM}		-	-	21	
Diode Forward Voltage	V_F	I_F = 7 A	-	1.75	2.0	V
Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = 7 A, dIF/dt = 200 A/µs, V_R = 400 V	-	70	-	ns
Reverse Recovery Charge	Q_{rr}		-	0.26	-	µC
Reverse Recovery Current	I_{RRM}		-	9	-	A

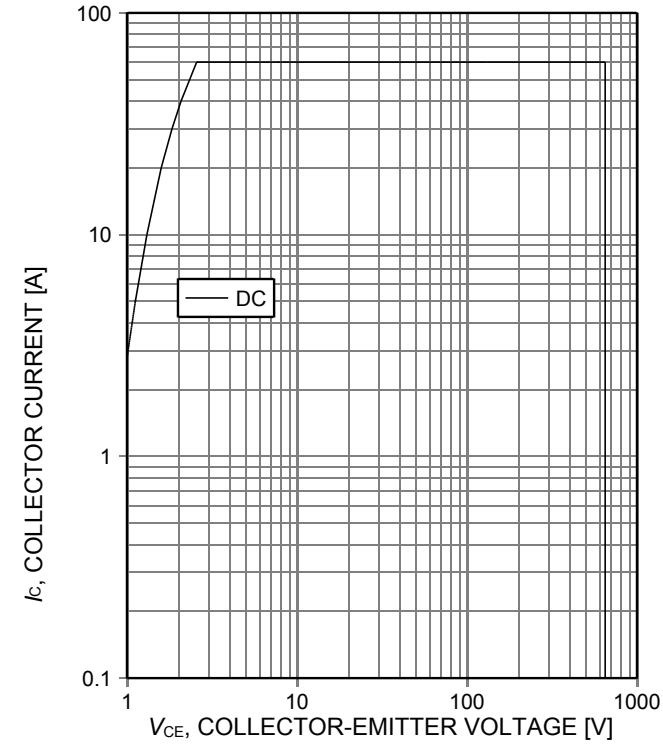


Figure 1. **Forward bias safe operating area** (D=0, T_C=25°C, T_{vj}≤175°C; V_{GE}=15V. Recommended use at V_{GE}≥7.5V)

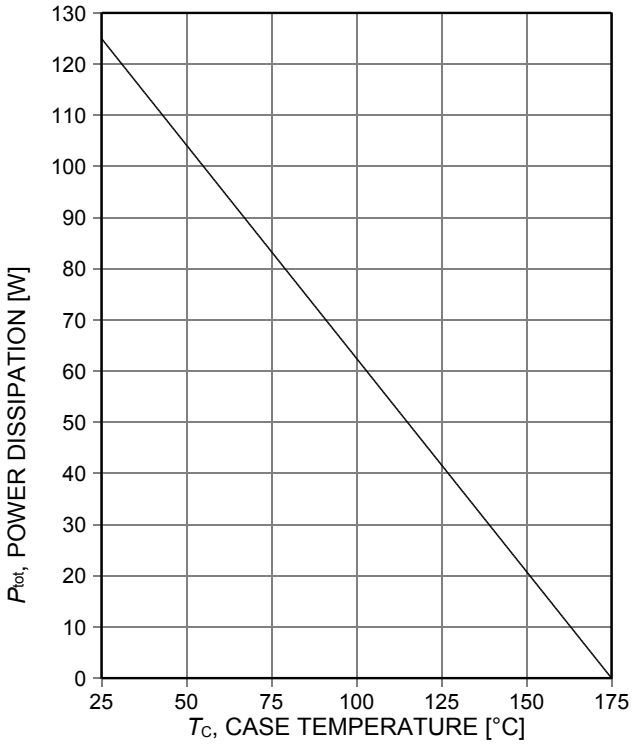


Figure 2. **Power dissipation as a function of case temperature** (T_{vj}≤175°C)

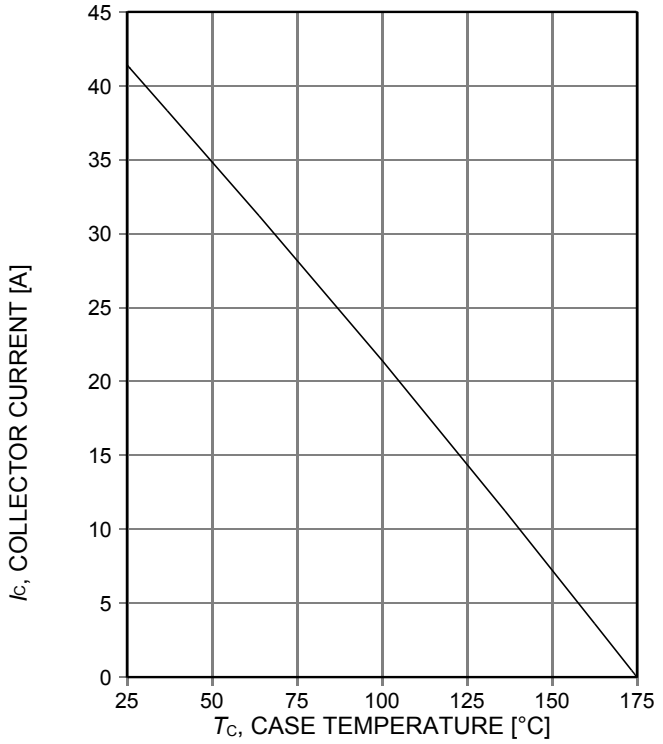


Figure 3. **Collector current as a function of case temperature**

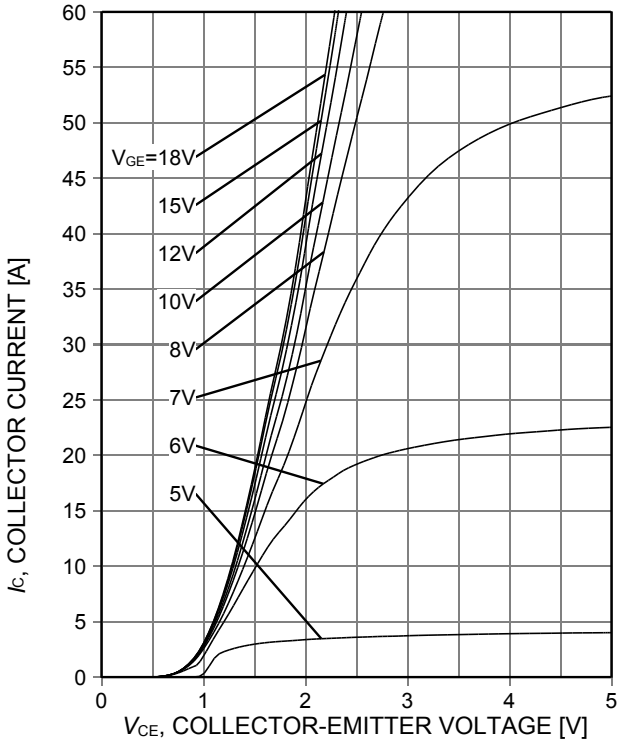


Figure 4. **Typical output characteristic**

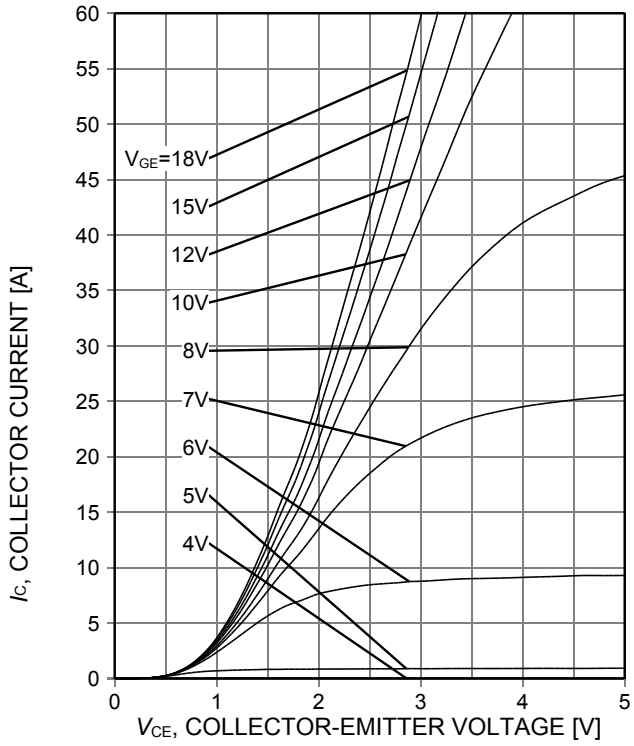


Figure 5. **Typical output characteristic** (T_{vj}=150°C)

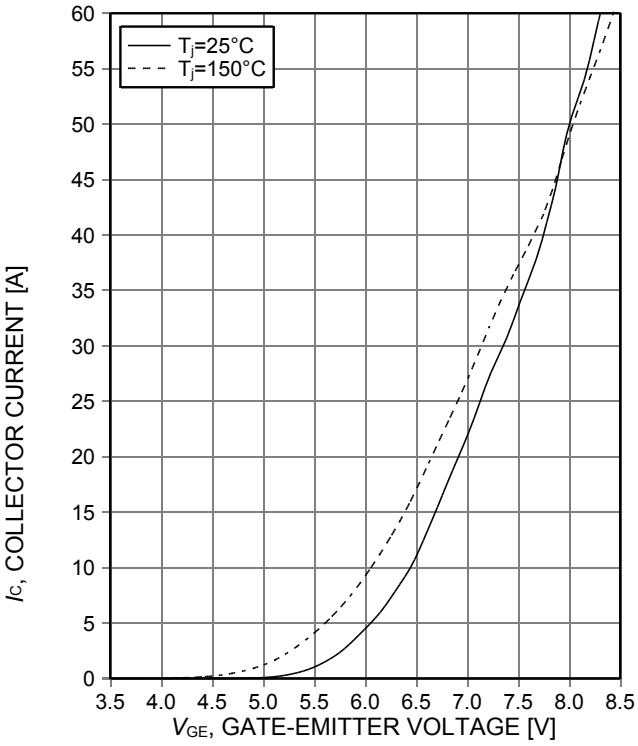


Figure 6. **Typical transfer characteristic** (V_{CE}=20V)

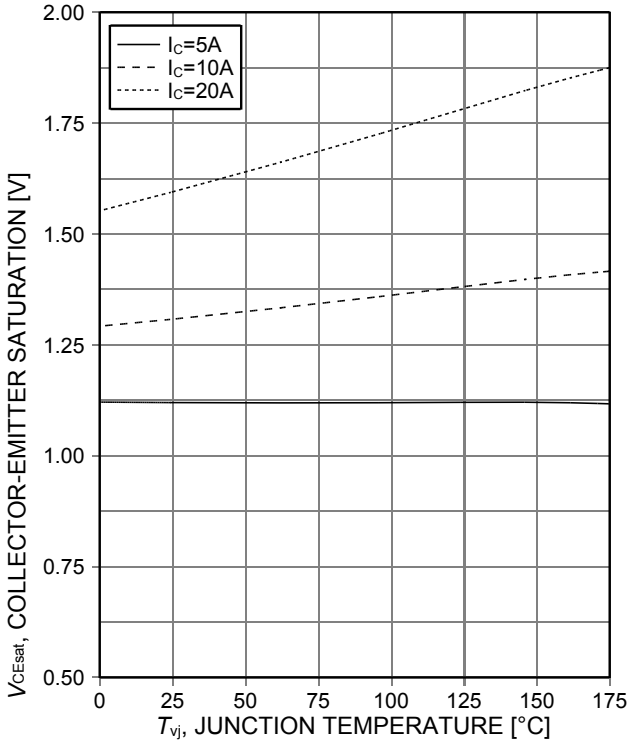


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**

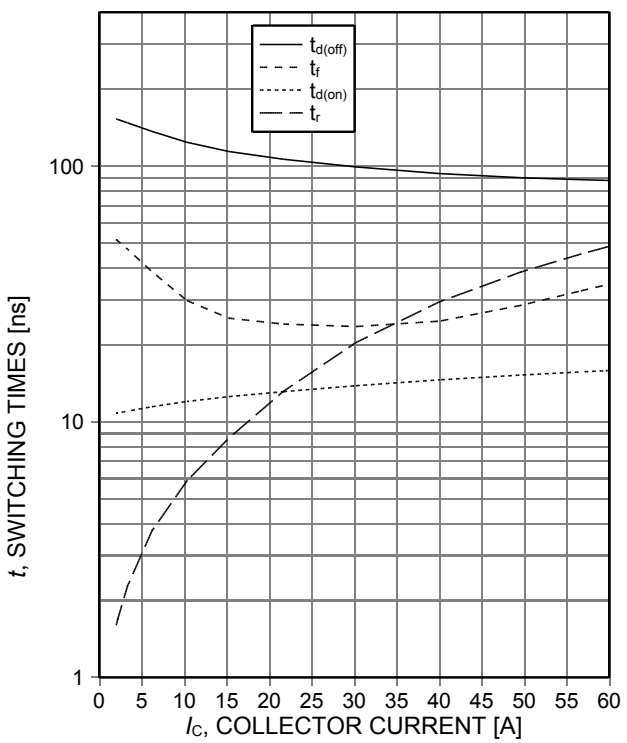


Figure 8. **Typical switching times as a function of collector current**

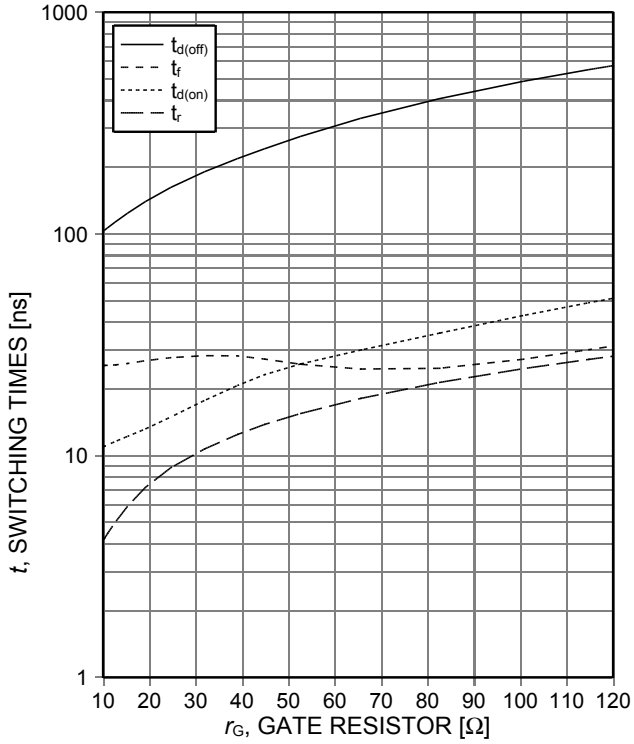


Figure 9. **Typical switching times as a function of gate resistor**

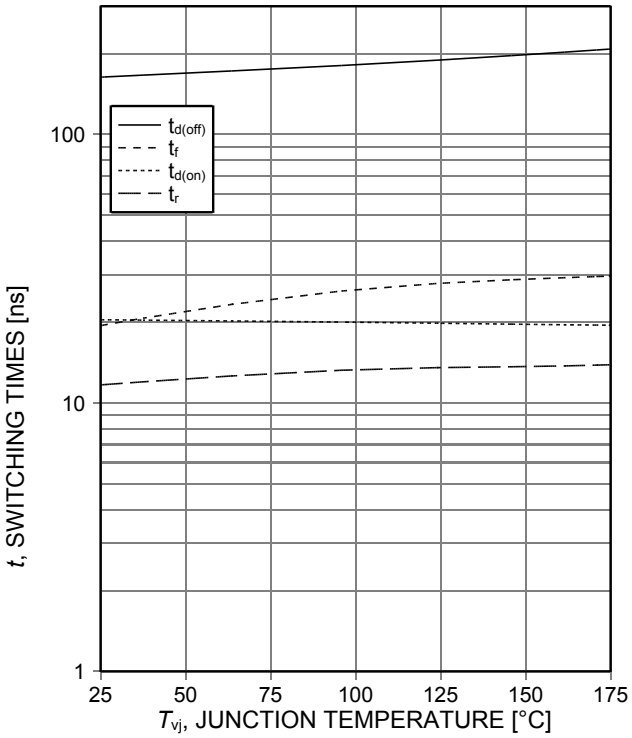


Figure 10. **Typical switching times as a function of junction temperature**

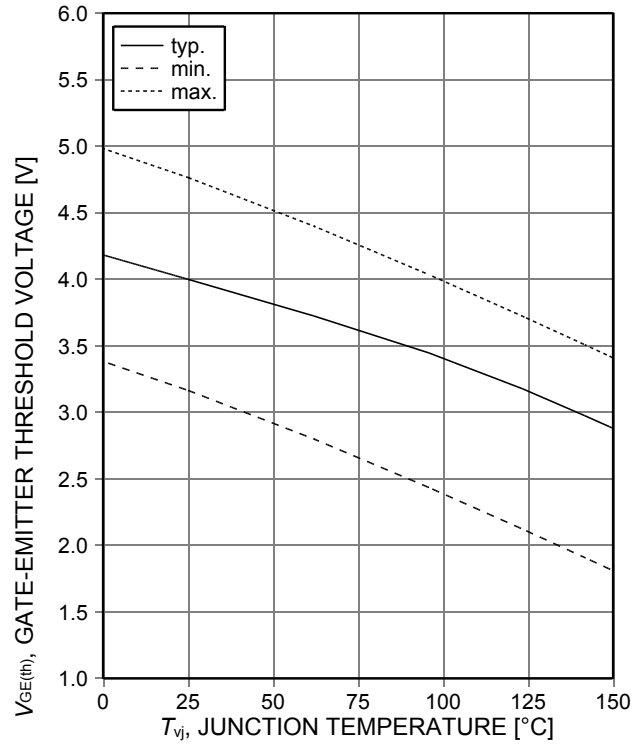


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**

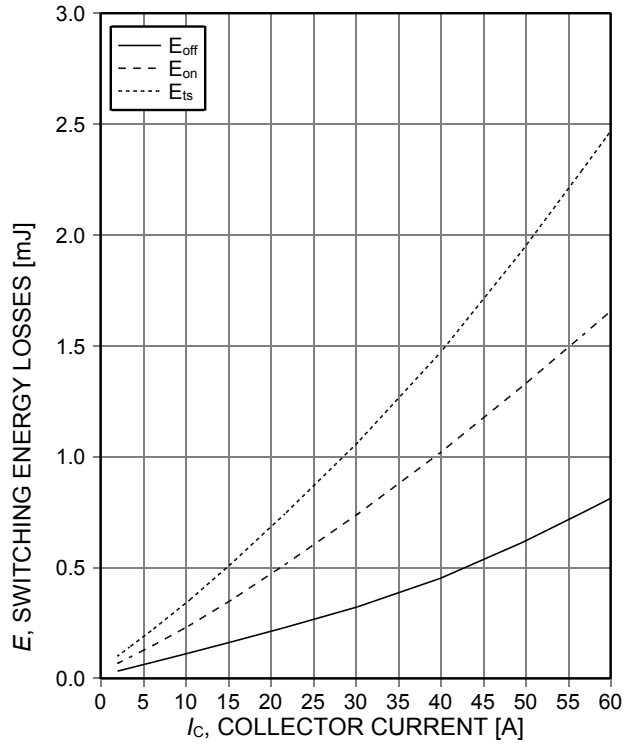


Figure 12. **Typical switching energy losses as a function of collector current**

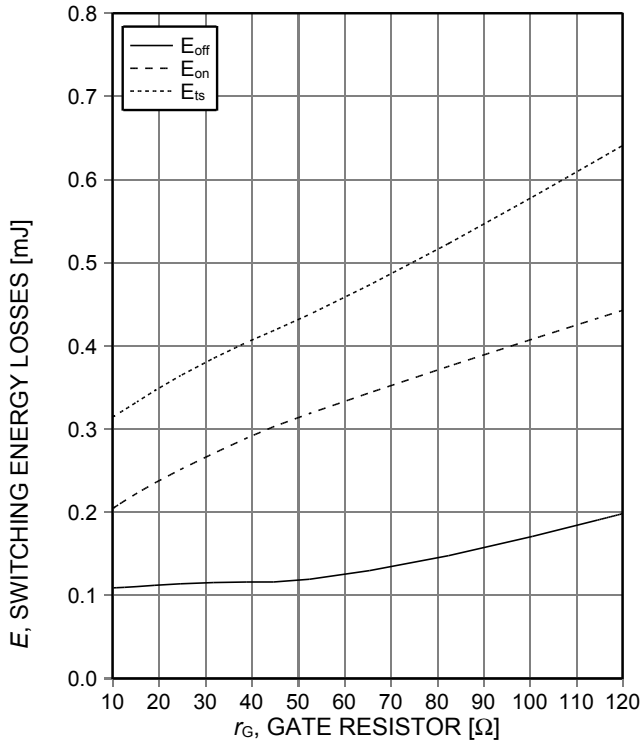


Figure 13. **Typical switching energy losses as a function of gate resistor**

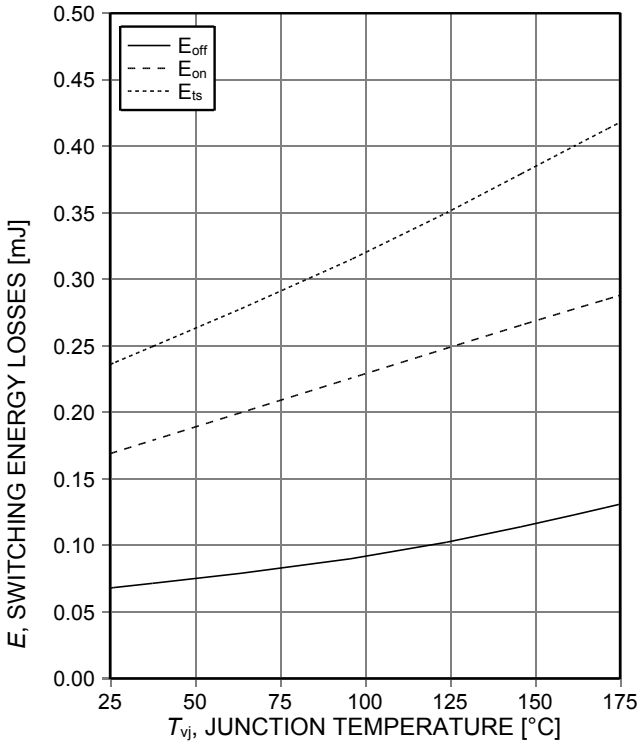


Figure 14. **Typical switching energy losses as a function of junction temperature**

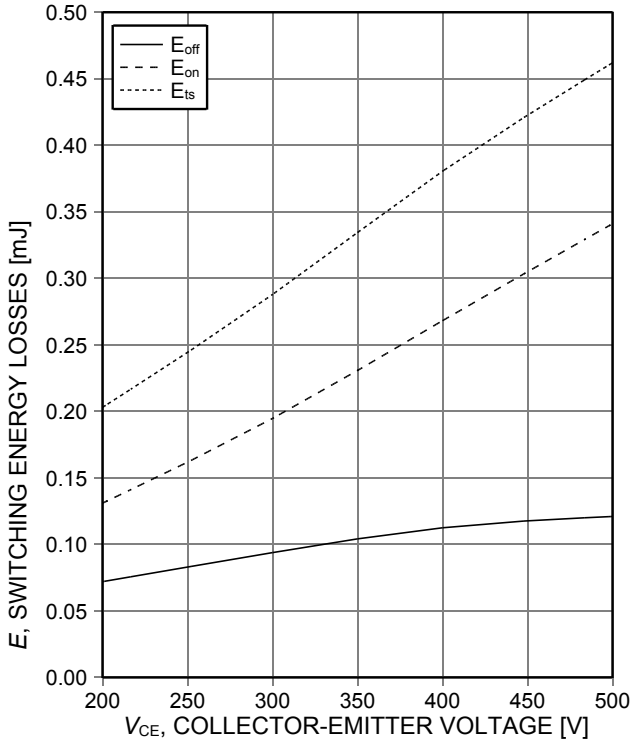


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**

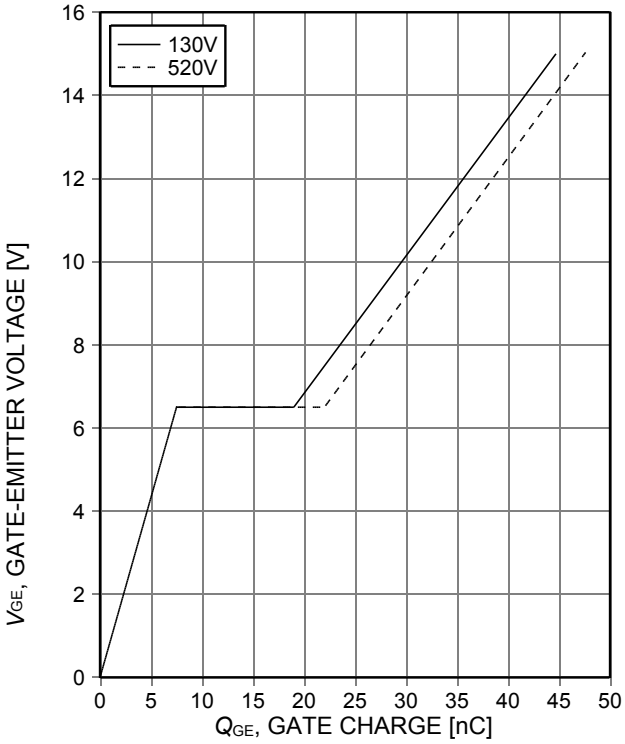


Figure 16. **Typical gate charge**

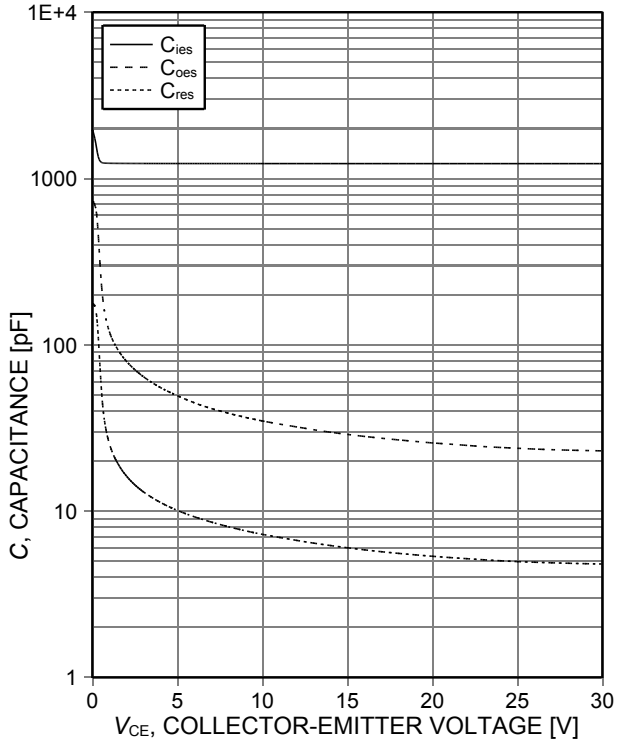


Figure 17. **Typical capacitance as a function of collector-emitter voltage**

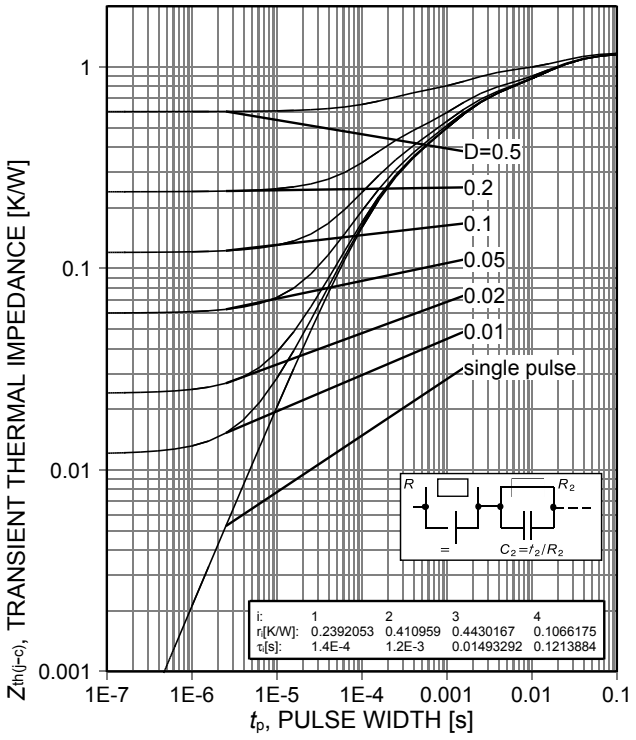


Figure 18. **IGBT transient thermal impedance**

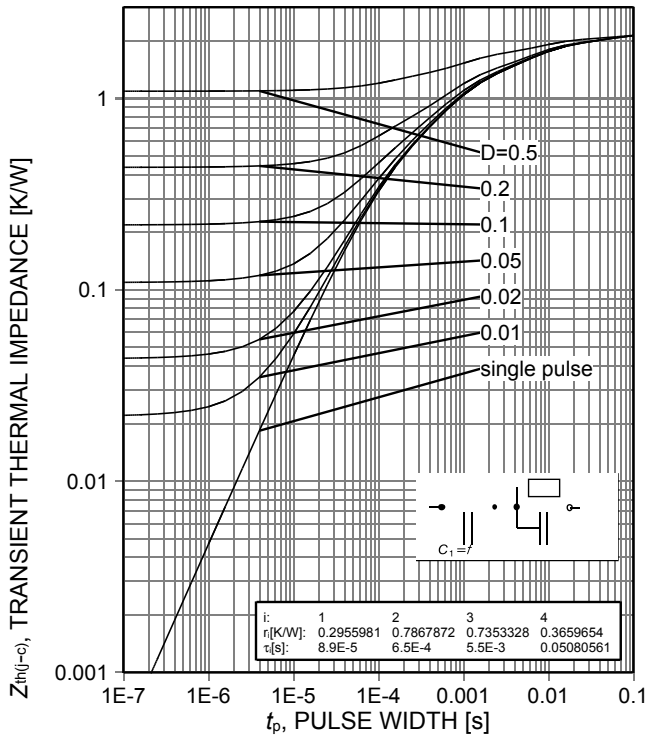


Figure 19. **Diode transient thermal impedance as a function of pulse width**

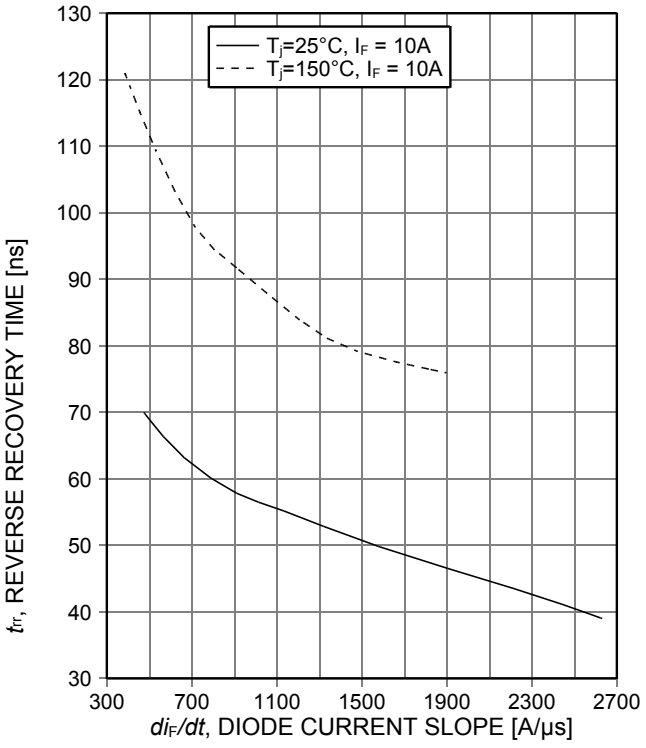
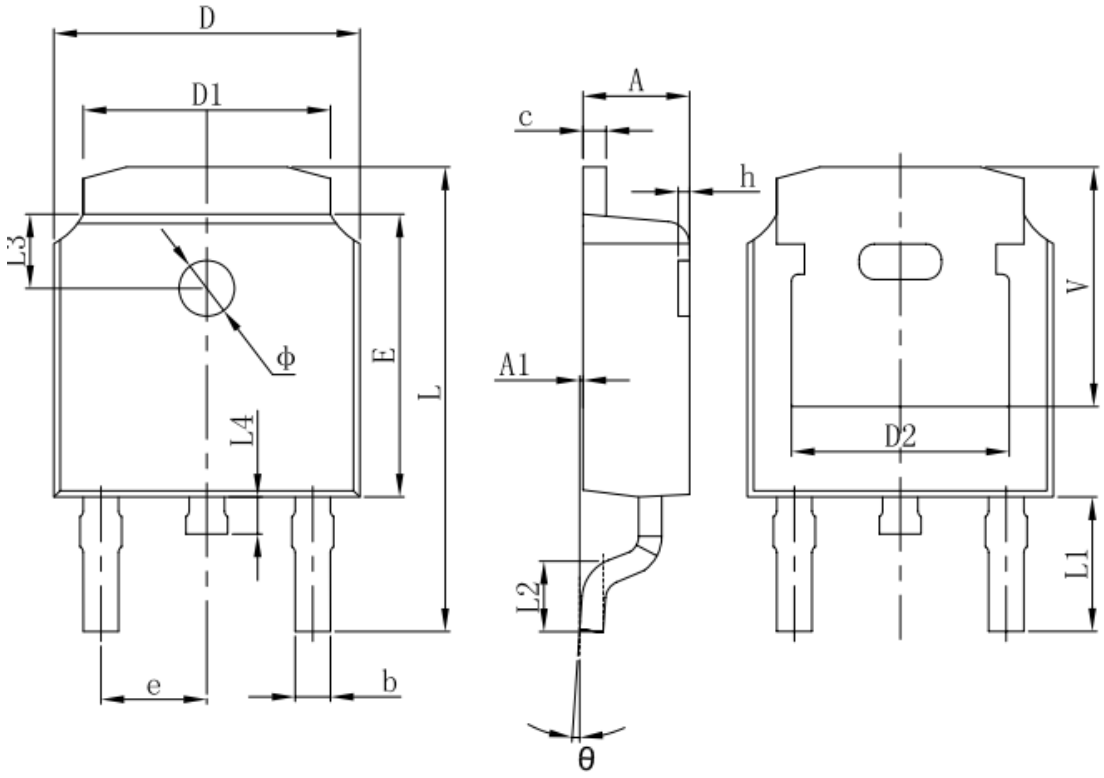


Figure 20. **Typical reverse recovery time as a function of diode current slope**

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.770	0.025	0.030
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250 REF.		0.207 REF.	

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